NSN 5962-01-341-0366

Memory Microcircuit - Page 1 of 2

View Online at https://aerobasegroup.com/nsn/5962-01-341-0366

Overall Height:

0.400 inches

Body Length:

1.280 inches

Body Width:

Between 0.220 inches and 0.310 inches

Body Height:

Between 0.140 inches and 0.185 inches

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Hermetically sealed and burn in and programmed and bipolar

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

16 input

Case Outline Source And Designator:

D-8 mil-m-38510

Current Rating Per Characteristic:

100.00 milliamperes output sink

Terminal Surface Treatment:

Solder

Product Name:

And-or invert gate array

Voltage Rating And Type Per Characteristic:

-500.0 millivolts power source and 12.0 volts power source

Time Rating Per Chacteristic:

45.00 nanoseconds propagation delay time, high to low level output and 45.00 nanoseconds propagation delay time, low to high level output

Memory Device Type:

Programmed

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

20 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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